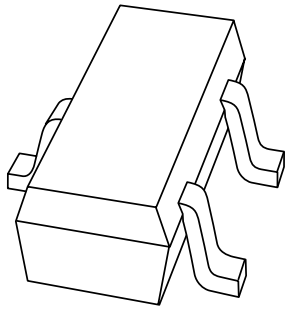


# DATA SHEET



## **BFQ67T** NPN 8 GHz wideband transistor

Preliminary specification

1999 Oct 18

# NPN 8 GHz wideband transistor

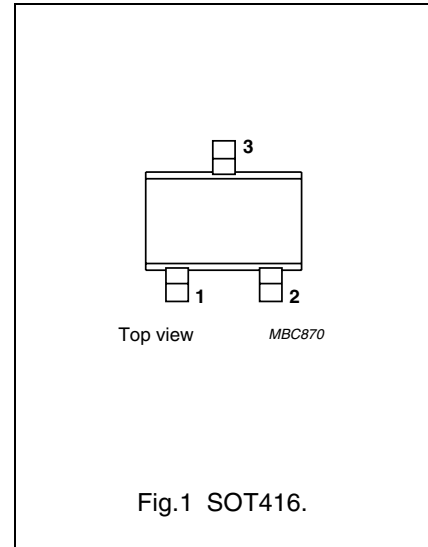
# BFQ67T

### FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT416 (SC75) envelope.

### PINNING

PIN	DESCRIPTION
Code: V2	
1	base
2	emitter
3	collector



### DESCRIPTION

NPN transistor in a plastic SOT416 (SC75) envelope.

It is designed for wideband applications such as satellite TV tuners and RF portable communications equipment up to 2 GHz.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–	10	V
$I_C$	DC collector current		–	–	50	mA
$P_{tot}$	total power dissipation	up to $T_s = 118\text{ °C}$ ; note 1	–	–	300	mW
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 5\text{ V}$ ; $T_j = 25\text{ °C}$	60	100	–	
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
$G_{UM}$	maximum unilateral power gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	13	–	dB
F	noise figure	$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	1.3	–	dB

### LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	10	V
$V_{EBO}$	emitter-base voltage	open collector	–	2.5	V
$I_C$	DC collector current		–	50	mA
$P_{tot}$	total power dissipation	up to $T_s = 118\text{ °C}$ ; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	150	°C
$T_j$	junction temperature		–	175	°C

### Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

## NPN 8 GHz wideband transistor

BFQ67T

## THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 118\text{ °C}$ ; note 1	190 K/W

## Note

- $T_s$  is the temperature at the soldering point of the collector tab.

## CHARACTERISTICS

$T_j = 25\text{ °C}$ , unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = 5\text{ V}$	–	–	50	nA
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 5\text{ V}$	60	100	–	
$C_c$	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	–	0.7	–	pF
$C_e$	emitter capacitance	$I_C = i_c = 0$ ; $V_{EB} = 0.5\text{ V}$ ; $f = 1\text{ MHz}$	–	1.3	–	pF
$C_{re}$	feedback capacitance	$I_C = 0$ ; $V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	–	0.5	–	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
$G_{UM}$	maximum unilateral power gain (note 1)	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	13	–	dB
		$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$ ; $I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	1.3	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	2	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$	–	2.2	–	dB
		$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $Z_s = 60\ \Omega$	–	2.5	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$	–	2.7	–	dB
		$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $Z_s = 60\ \Omega$	–	3	–	dB

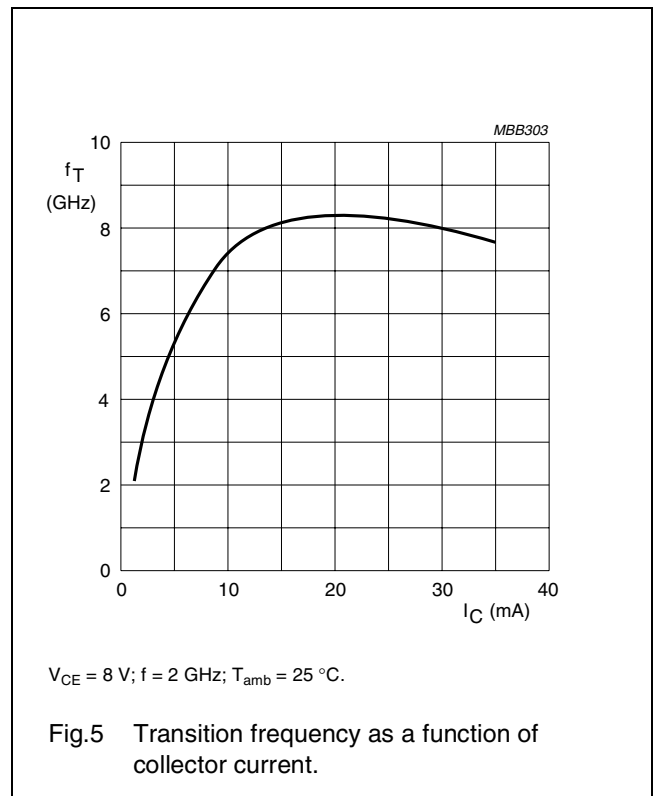
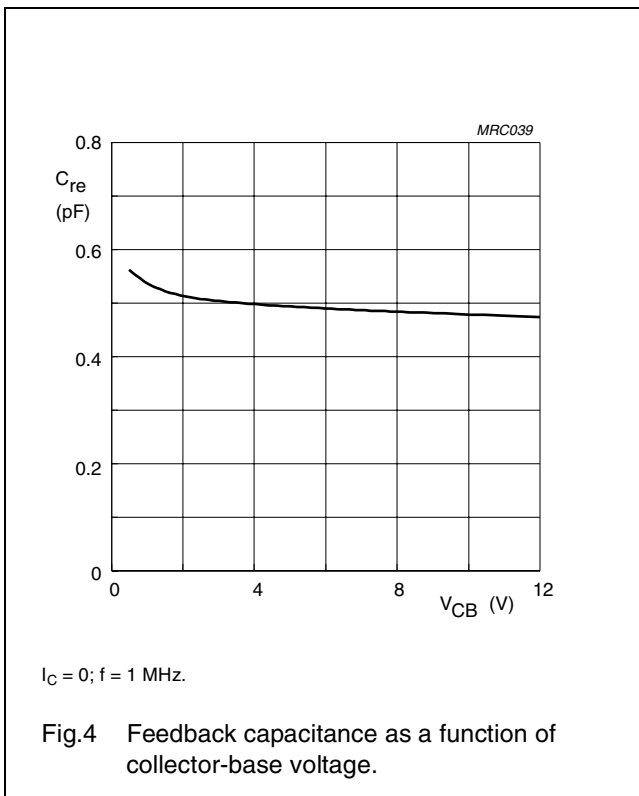
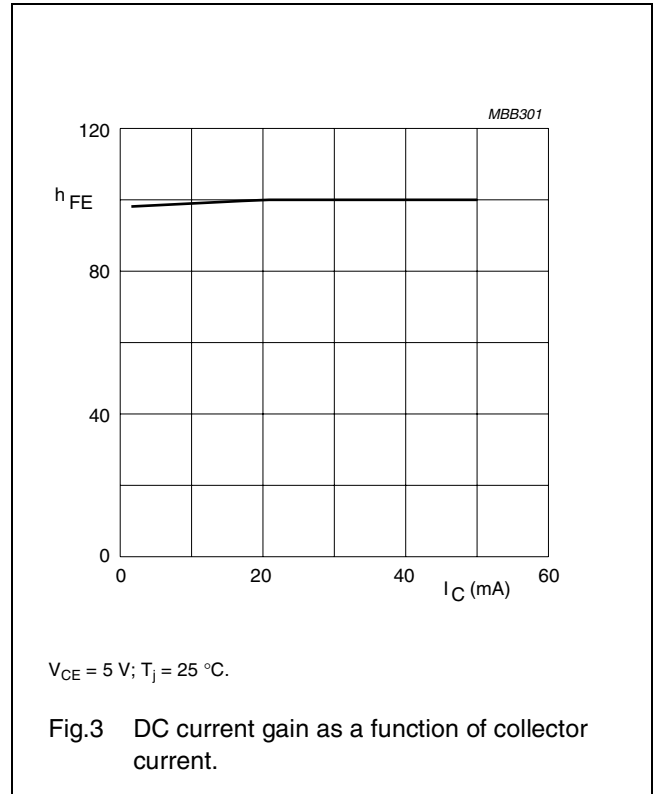
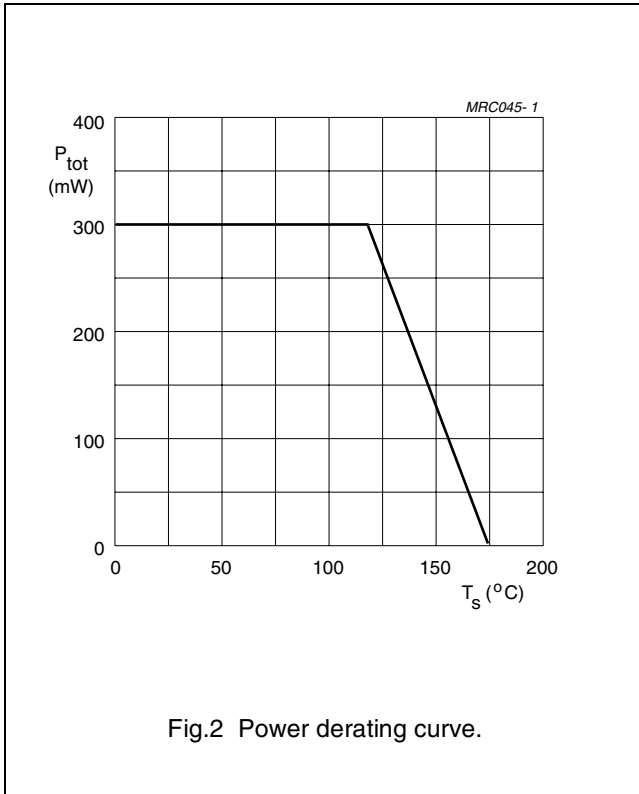
## Note

- $G_{UM}$  is the maximum unilateral power gain, assuming  $S_{12}$  is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ dB.}$$

NPN 8 GHz wideband transistor

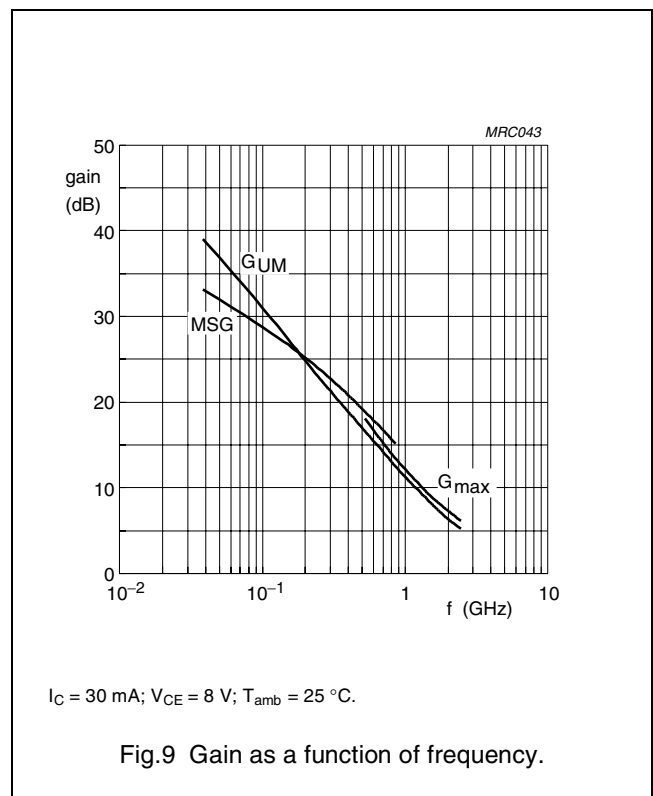
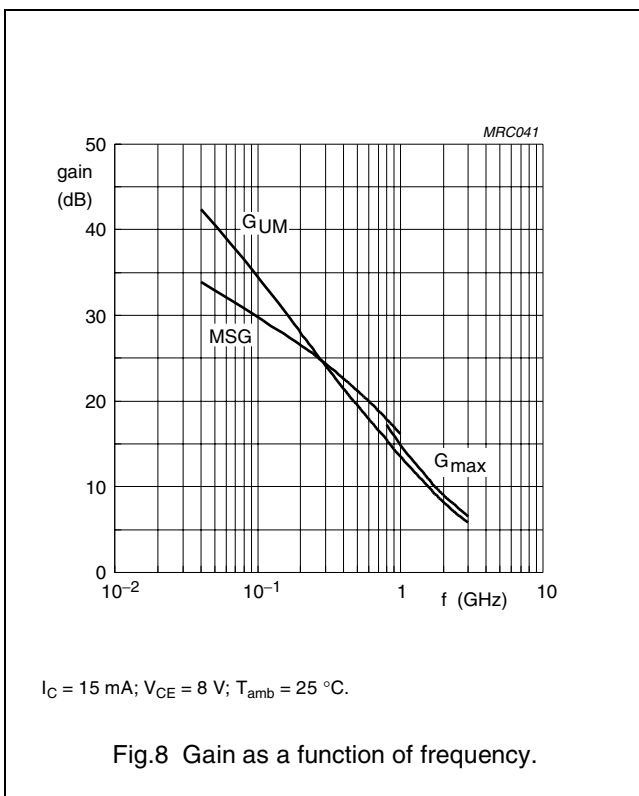
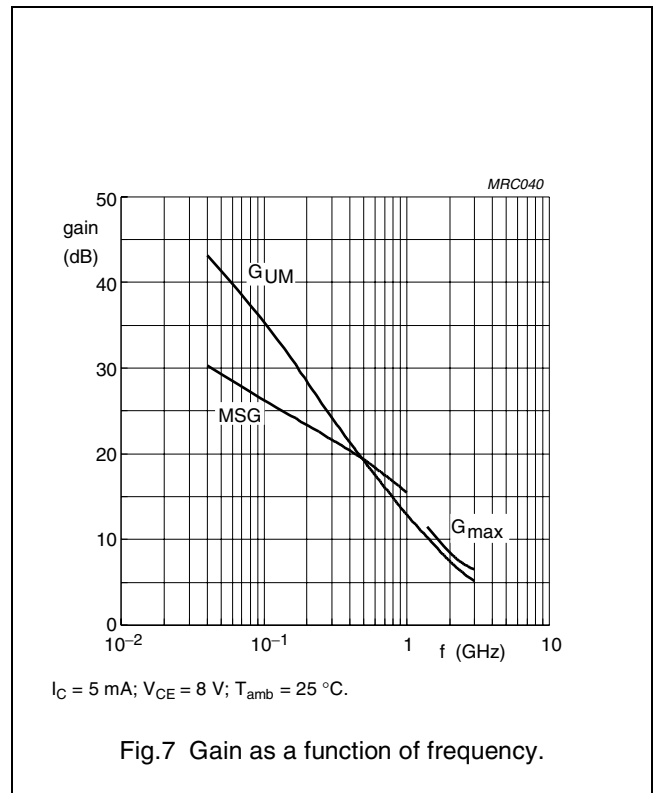
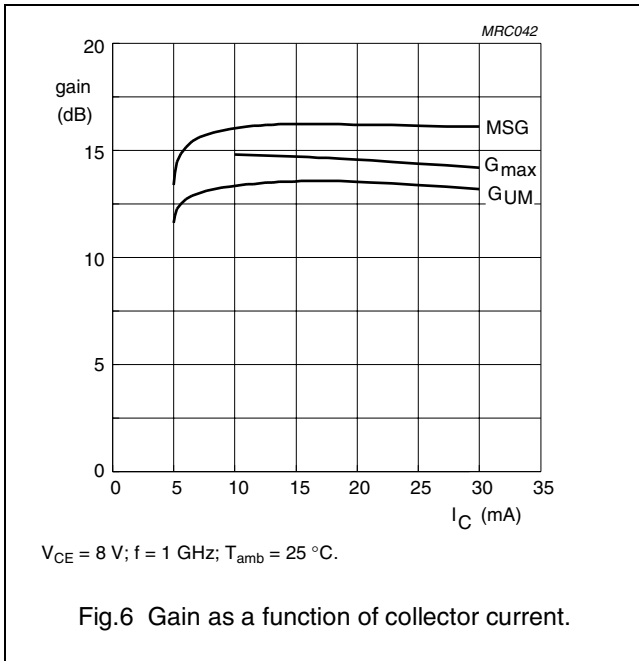
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NPN 8 GHz wideband transistor

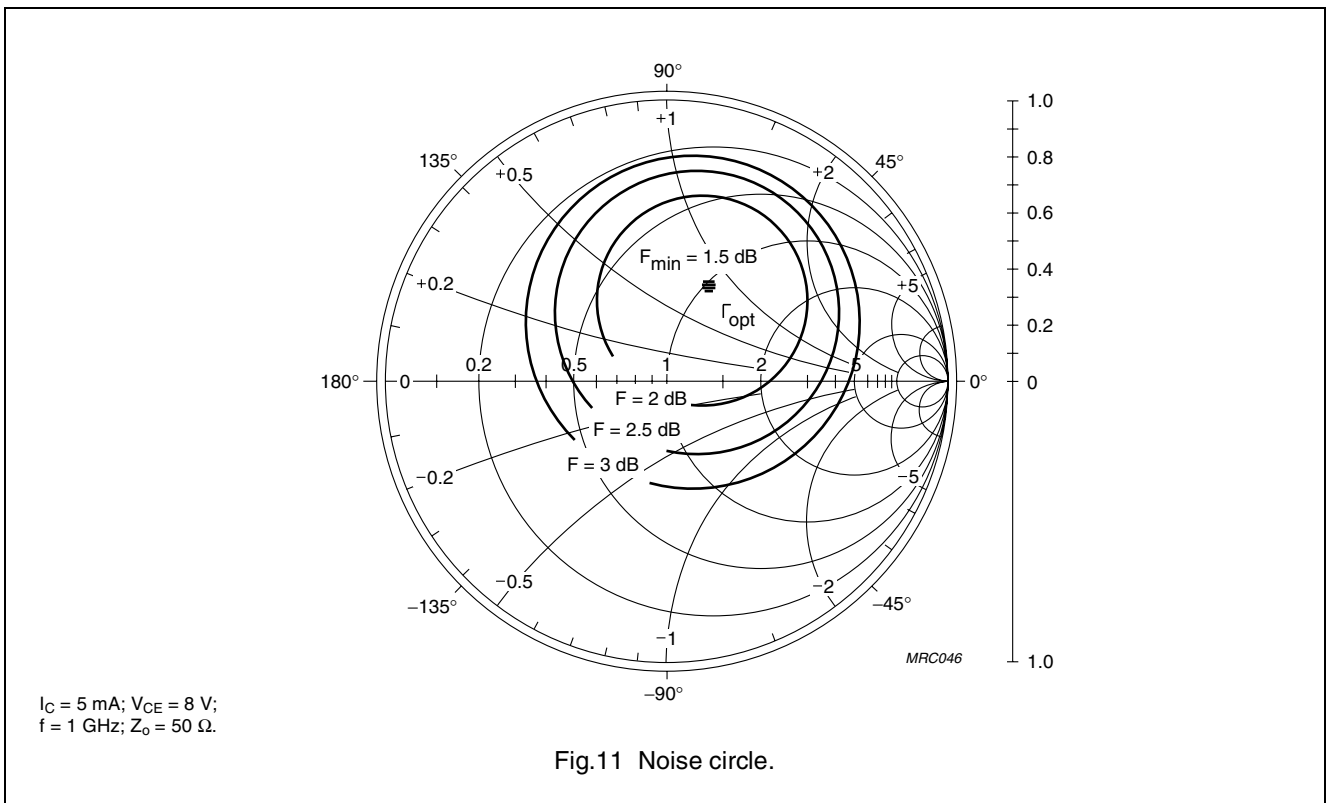
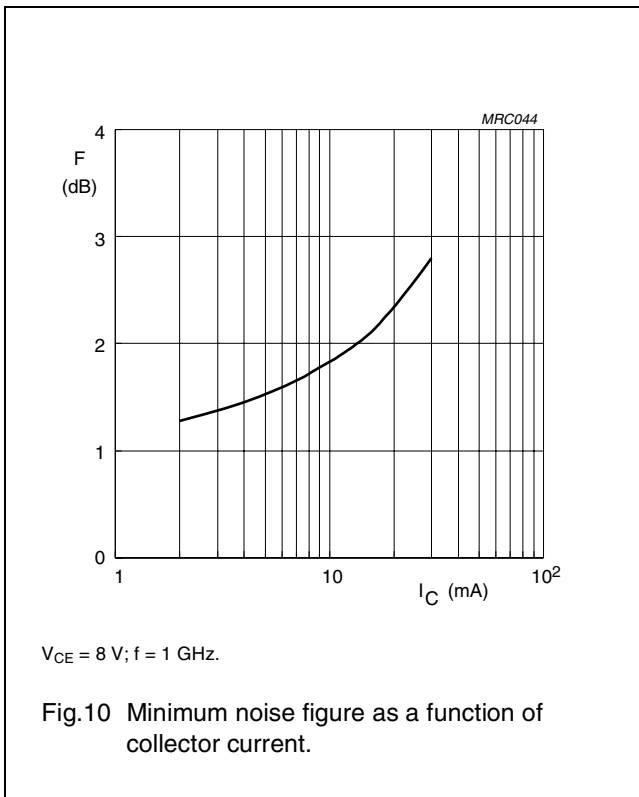
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In Figs 6 to 9,  $G_{UM}$  = maximum unilateral power gain;  $MSG$  = maximum stable gain;  $G_{max}$  = maximum available gain.



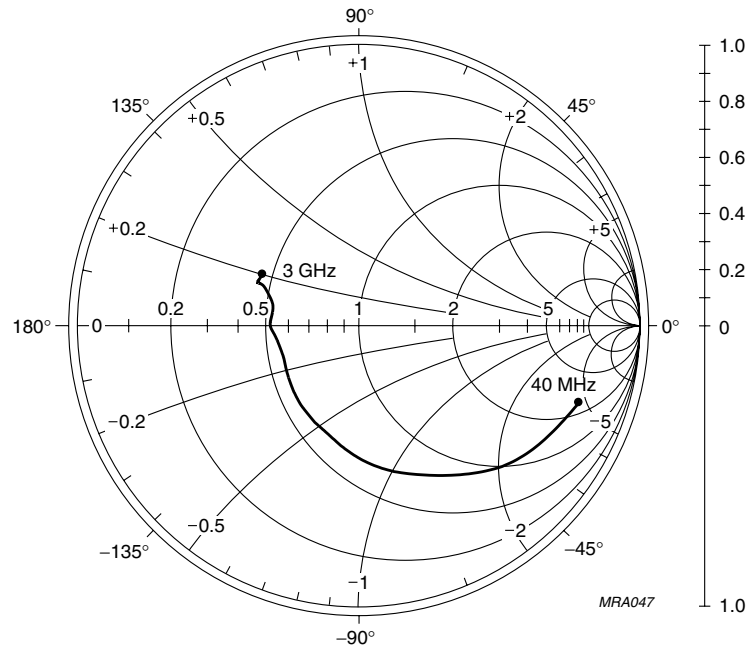
NPN 8 GHz wideband transistor

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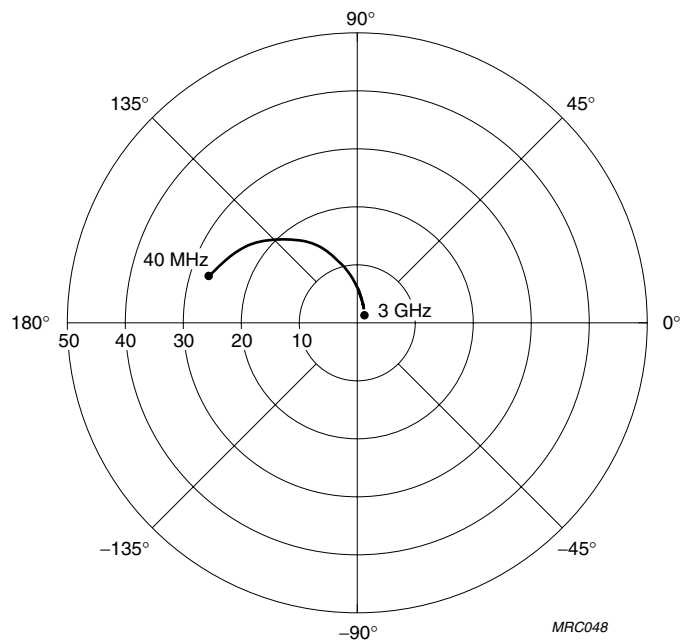
NPN 8 GHz wideband transistor

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$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}; Z_0 = 50 \Omega.$

Fig.12 Common emitter input reflection coefficient ( $S_{11}$ ).

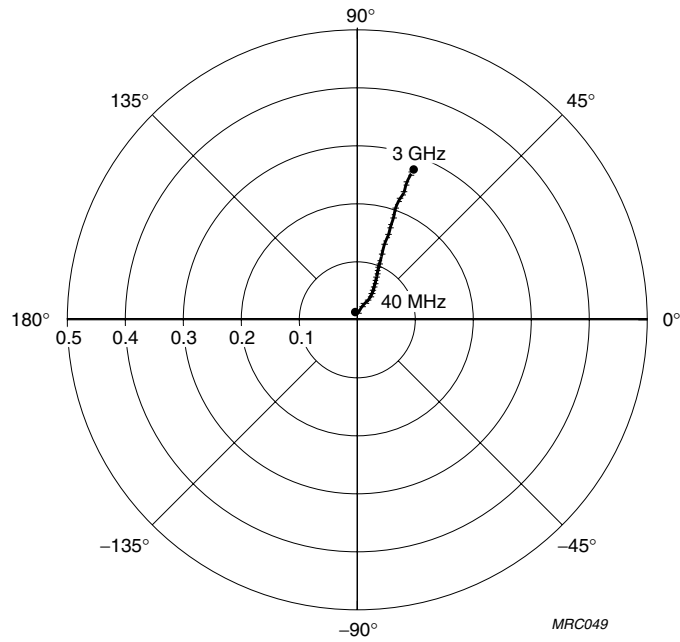


$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.13 Common emitter forward transmission coefficient ( $S_{21}$ ).

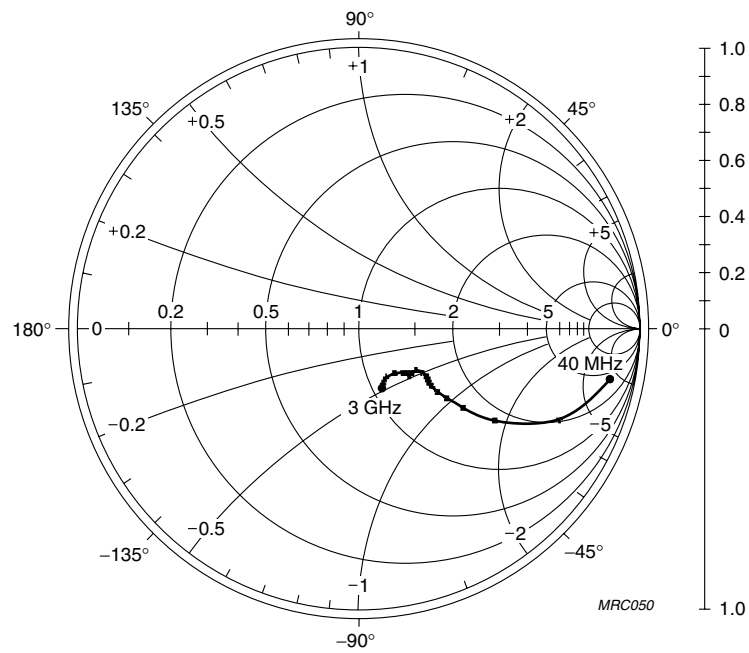
NPN 8 GHz wideband transistor

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$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.14 Common emitter reverse transmission coefficient ( $S_{12}$ ).



$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}; Z_0 = 50 \Omega.$

Fig.15 Common emitter output reflection coefficient ( $S_{22}$ ).



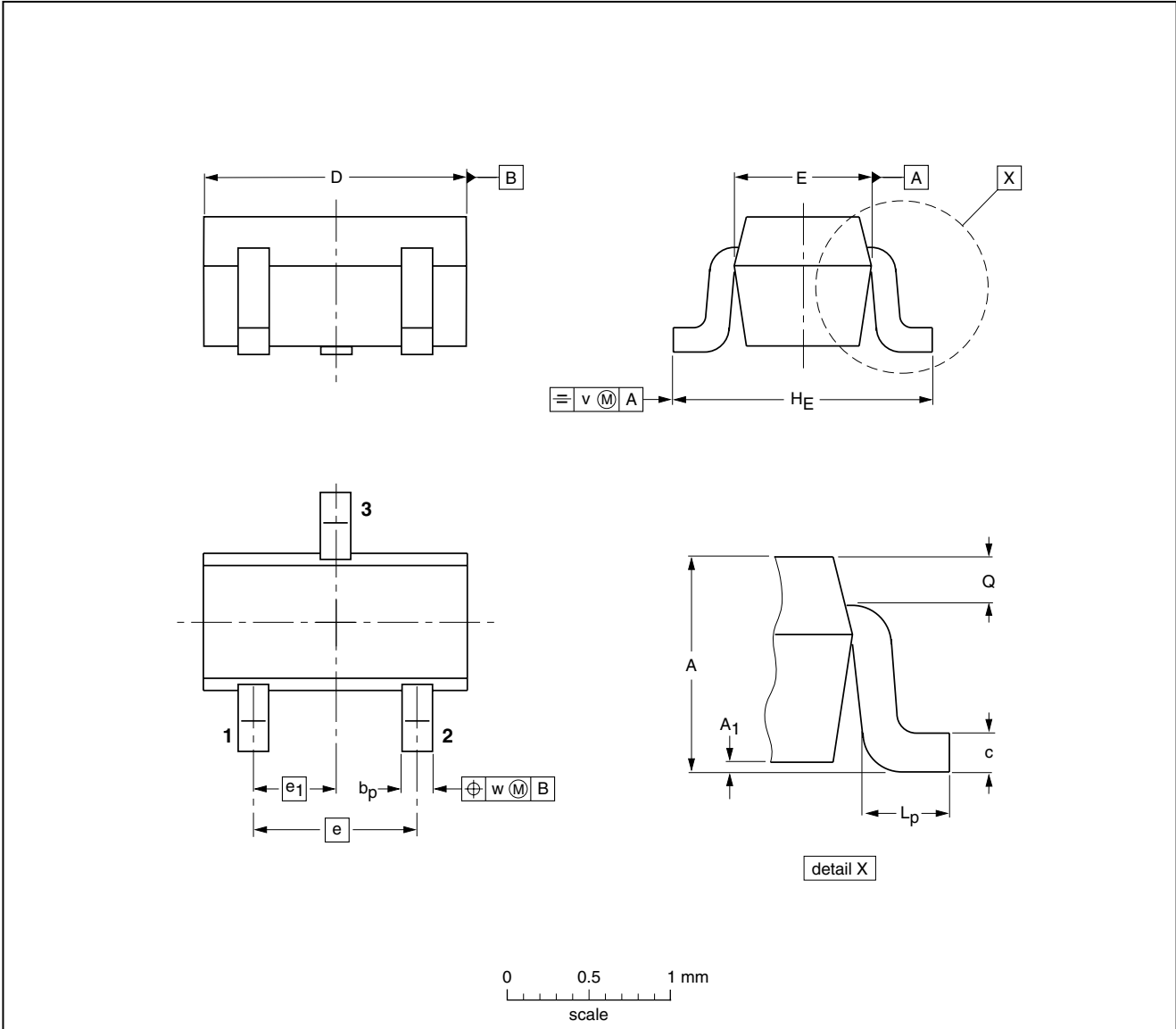
NPN 8 GHz wideband transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

## NPN 8 GHz wideband transistor

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Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
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